

2SB1220G

Silicon PNP epitaxial planar type

For high breakdown voltage low-noise amplification Complementary to 2SD1821G

■ Features

- ullet High collector-emitter voltage (Base open) V_{CEO}
- Low noise voltage NV
- S-Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

■ Absolute Maximum Ratings T_a = 25°C

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V_{CBO}	-150	V	
Collector-emitter voltage (Base open)	V _{CEO}	-150	V	
Emitter-base voltage (Collector open)	$V_{\rm EBO}$	-5	V	
Collector current	I_{C}	-50	mA	
Peak collector current	I_{CP}	-100	mA	
Collector power dissipation	P _C	150	mW	
Junction temperature	T _j	150	°C	
Storage temperature	T _{stg}	-55 to +150	°C×C	

Package

- Code SMini3-F2
- Marking Symbol: I
- Pin Name
 - 1. Base
 - 2. Emitter
 - 3. Collector

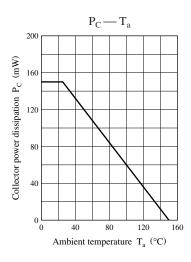
■ Electrical Characteristics $T_a = 25$ °C ± 3 °C

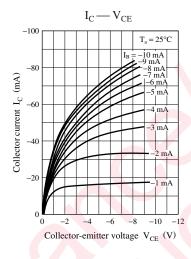
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = -100 \mu\text{A}, I_B = 0$	-150			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = -10 \mu\text{A}, I_C = 0$	-5			V
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = -100 \text{ V}, I_E = 0$			-1	μΑ
Forward current transfer ratio *	h _{FE}	$V_{CE} = -5 \text{ V}, I_{C} = -10 \text{ mA}$	130		450	_
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = -30 \text{ mA}, I_B = -3 \text{ mA}$			-1	V
Transition frequency	f_T	$V_{CB} = -10 \text{ V}, I_E = 10 \text{ mA}, f = 200 \text{ MHz}$		200		MHz
Collector output capacitance	C _{ob}	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		4		pF
(Common base, input open circuited)		S XXX				
Noixe voltage	NV	$V_{CE} = -10 \text{ V}, I_{C} = -1 \text{ mA}, G_{V} = 80 \text{ dB}$		150		mV
		$R_g = 100 \text{ k}\Omega$, Function = FLAT				

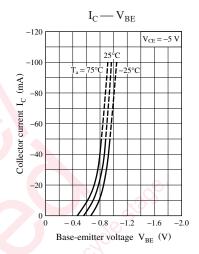
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

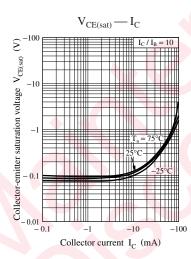
2. *: Rank classification

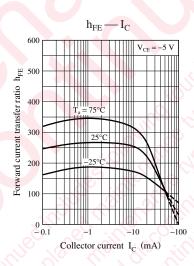
Rank	R	S	Т
h_{FE}	130 to 220	185 to 330	260 to 450

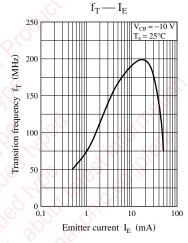


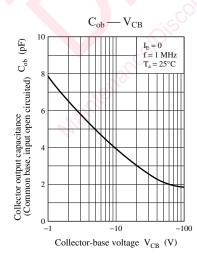






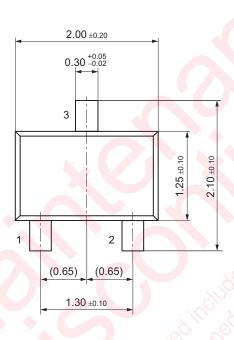


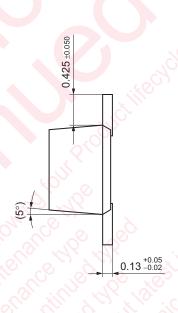


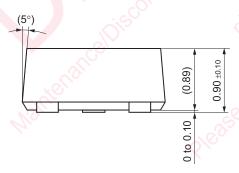


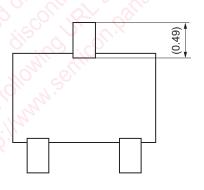
2 SJC00354AED

SMini3-F2 Unit: mm









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